

Patent Search Results

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Document ID: US 20040184931

Search: 60 and (spacer near recess\$3)

US PCT EP USAT

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19. 60 and (spacer near recess\$3)

20. 60 and (spacer near recess\$3)

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U	Document ID	Issue Date	Pages	Title	Current OR	Current AR	Relevancy	C	Inventor	S	C	P	N	3
19.	US 20011227	29		Methods of forming	438/183	257/E21.444;			Uh, Hyung-Soo et al.	<input checked="" type="checkbox"/>				
20.	US 20010906	16		Semiconductor device and	257/317	257/E21.682			Meguro, Hisataka	<input checked="" type="checkbox"/>				
21.	US 20010726	16		Method of making insulator	438/595	257/E21.358;			Mouli, Chandra V. et	<input checked="" type="checkbox"/>				
22.	US 20010726	18		Reduced gate length transistor	438/302	257/E21.345;			Bothra, Subhas et al.	<input checked="" type="checkbox"/>				
23.	US 6812103	21		Methods of fabricating a	438/300	438/302;			Wang, Hongmei et al.	<input checked="" type="checkbox"/>				
24.	US 6797556	23		MOS transistor structure and	438/231	257/288;			Murthy, Anand et al.	<input checked="" type="checkbox"/>				
25.	US 6790717	6		Method for producing a	438/182	257/309;			Behammer, Dag	<input checked="" type="checkbox"/>				
26.	US 6780694	24		MOS transistor	438/182	257/133;			Doris, Bruce B. et al.	<input checked="" type="checkbox"/>				
27.	US 6764966	12		Spacers with a graded	438/785	438/578;			En, William George et	<input checked="" type="checkbox"/>				
28.	US 6700205	11		Semiconductor devices	257/776	257/300;			Tang, Sanh D. et al.	<input checked="" type="checkbox"/>				
29.	US 6673665	14		Semiconductor device having	438/233	257/E21.634;			Wieczorek, Karsten et	<input checked="" type="checkbox"/>				
30.	US 6656764	16		Process for integration of a	438/104	257/E21.633;			Wang, Ming-Fang et al	<input checked="" type="checkbox"/>				
31.	US 6627504	8		Stacked double sidewall	438/303	438/267;			Bertrand, Jacques J. et	<input checked="" type="checkbox"/>				
32.	US 6613621	27		Methods of forming	438/183	257/E21.444;			Uh, Hyung-Soo et al.	<input checked="" type="checkbox"/>				
33.	US 6595820	16		Field emitter cell and array	445/24	313/309			Hsu, David S. Y. et al.	<input checked="" type="checkbox"/>				
34.	US 6576507	10		Selectively removable filler	438/234	257/E21.696			Bandy, Kenneth A. et	<input checked="" type="checkbox"/>				
35.	US 6573139	12		Method of fabricating cell of	438/257	257/315;			Lee, Seong-soo et al.	<input checked="" type="checkbox"/>				
36.	US 6573136	10		Isolating a vertical gate	438/242	257/E21.649;			Hummler, Klaus	<input checked="" type="checkbox"/>				

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L63: (120) 60 and (spacer near2 recess\$3)
L64: (73) 60 and (spacer near recess\$3)
L65: (1) "6108988".PN.
L66: (1) "6071782".PN.
L67: (1) "5920783".PN.
L68: (1) "5882973".PN.

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U	Document ID	Issue Date	Pages	Title	Current OR	Current NR	Retrieval C	Inventor	S	C	P	N	R
37	<input checked="" type="checkbox"/> US 6551887	20030422	11	Method of forming a spacer	438/305	257/E21.435; 257/E21.100;		Kwon; Hyung-Shin et al.	<input checked="" type="checkbox"/>				
38	<input checked="" type="checkbox"/> US 6541815	20030401	22	High-density dual-cell flash	257/315	257/330; 257/E21.100;		Mandelman; Jack A. et al.	<input checked="" type="checkbox"/>				
39	<input checked="" type="checkbox"/> US 6521964	20030218	18	Device having spacers for	257/413	257/900;		Jan; Chia-Hong et al.	<input checked="" type="checkbox"/>				
40	<input checked="" type="checkbox"/> US 6512266	20030128	13	Method of fabricating SiO ₂	257/333	257/340; 257/E21.100;		Deshpande; Sadanand	<input checked="" type="checkbox"/>				
41	<input checked="" type="checkbox"/> US 6509618	20030121	18	Device having thin first	257/413	257/900;		Jan; Chia-Hong et al.	<input checked="" type="checkbox"/>				
42	<input checked="" type="checkbox"/> US 6504210	20030107	9	Fully encapsulated damascene	257/344	257/408;		Divakaruni; Rameshankar et al.	<input checked="" type="checkbox"/>				
43	<input checked="" type="checkbox"/> US 6501526	20021231	21	Flat panel display apparatus	349/155	349/156;		Oh; Jae Yeol	<input checked="" type="checkbox"/>				
44	<input checked="" type="checkbox"/> US 6495900	20021217	18	Insulator for electrical	257/522	257/410; 257/E21.100;		Mouli; Chandra V. et al.	<input checked="" type="checkbox"/>				
45	<input checked="" type="checkbox"/> US 6489215	20021203	16	Method of making insulator	438/400	257/E21.358;		Mouli; Chandra V. et al.	<input checked="" type="checkbox"/>				
46	<input checked="" type="checkbox"/> US 6479377	20021112	13	Method for making	438/618	257/E21.507;		Tang; Sanh D. et al.	<input checked="" type="checkbox"/>				
47	<input checked="" type="checkbox"/> US 6348419	20020219	7	Modification of the wet	438/753	257/E21.293;		Grellner; Frank et al.	<input checked="" type="checkbox"/>				
48	<input checked="" type="checkbox"/> US 6235598	20010522	17	Method of using thick first	438/303	257/E21.199;		Jan; Chia-Hong et al.	<input checked="" type="checkbox"/>				
49	<input checked="" type="checkbox"/> US 6235589	20010522	15	Method of making	438/267	257/E21.682;		Meguro; Hisataka	<input checked="" type="checkbox"/>				
50	<input checked="" type="checkbox"/> US 6214679	20010410	21	Cobalt salicidation method on	438/299	257/E21.165;		Murthy; Anand et al.	<input checked="" type="checkbox"/>				
51	<input checked="" type="checkbox"/> US 6190996	20010220	21	Method of making an	438/400	257/522;		Mouli; Chandra V. et al.	<input checked="" type="checkbox"/>				
52	<input checked="" type="checkbox"/> US 6188117	20010213	18	Method and device for	257/413	257/E21.199;		Jan; Chia-Hong et al.	<input checked="" type="checkbox"/>				
53	<input checked="" type="checkbox"/> US 6168491	20010102	16	Method of forming field	445/24	445/50;		Hsu; David S. Y. et al.	<input checked="" type="checkbox"/>				
54	<input checked="" type="checkbox"/> US 6165826 A	20001226	29	Transistor with low resistance	438/231	257/E21.148;		Chau; Robert S. et al.	<input checked="" type="checkbox"/>				

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- L63: (120) 60 and (spacer near 2 recesses)
 - L64: (7) 60 and (spacer near recess)
 - L65: (1) "6108988".PN.
 - L66: (1) "6071782".PN.
 - L67: (1) "5920783".PN.
 - L68: (1) "5882973" PN

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U	Document ID	Issue Date	Pages	Title	Current OR	Current XR	Retrieval C	Inventor	S	C	P	3
35	US 6159065 A	20001212	15	Method for manufacturing a	445/24	445/23		Jung; Sung Jae et al.	✓	✓	✓	✓
36	US 6124177 A	20000926	9	Method for making deep	438/305	257/410;		Lin; Chrong Jung et al.	✓	✓	✓	✓
37	US 6107141 A	20000822	11	Flash EEPROM	438/267	438/257		Hsu; Louis Lu-Chen et	✓	✓	✓	✓
38	US 6084245 A	20000704	16	Field emitter cell and array	257/10	313/309;		Hsu; David S. Y. et al.	✓	✓	✓	✓
39	US 6074921 A	20000613	25	Self-aligned processing of	438/299	257/E21.31;		Lin; Xi-Wei	✓	✓	✓	✓
40	US 5953612 A	19990914	26	Self-aligned silicidation	438/299	257/E21.004;		Lin; Xi-Wei et al.	✓	✓	✓	✓
41	US 5910912 A	19990608	12	Flash EEPROM with	365/185.01	257/321;		Hsu; Louis Lu-Chen et	✓	✓	✓	✓
42	US 5904508 A	19990518	16	Semiconductor device and a	438/151	257/E21.413;		Codama; Mitsuumi et	✓	✓	✓	✓
43	US 5736435 A	19980407	8	Process for fabricating a fully	438/151	257/E21.415;		Venkatesan; Suresh et	✓	✓	✓	✓
44	US 5619097 A	19970408	76	Panel display with dielectric	313/495	313/309;		Jones; Gary W.	✓	✓	✓	✓
45	US 5587623 A	19961224	75	Field emitter structure and	313/497	313/309;		Jones; Gary W.	✓	✓	✓	✓
46	US 5548181 A	19960820	78	Field emission device	313/309	313/495;		Jones; Gary W.	✓	✓	✓	✓
47	US 5529524 A	19960625	78	Method of forming a spacer	445/24	257/213;		Jones; Gary W.	✓	✓	✓	✓
48	US 5298444 A	19940329	8	Method for manufacturing a	438/571	257/213;		Ristow; Dietrich	✓	✓	✓	✓
49	US 5220186 A	19930615	12	Semiconductor device with a	257/284	257/280;		Kasai; Nobuyuki et al.	✓	✓	✓	✓
50	US 5089434 A	19920218	18	Mask surrogate	438/274	257/E21.033;		Hollinger; Theodore G.	✓	✓	✓	✓
51	US 5045903 A	19910903	22	Topographic pattern	257/339	257/341;		Meyer; Theodore O. et	✓	✓	✓	✓
52	US 4932693 A	19900612	10	Gate latch assembly and hinge	292/205	16/299;		Schwartz; Bruce H.	✓	✓	✓	✓

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